WNSC5D10650D



Silicon Carbide Diode Rev.01 - 17 October 2022

Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO252 (DPAK) plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	e maximum rating						
V_{RRM}	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 140 °C; Fig. 1; Fig. 2; Fig. 3		10		A	
Tj	junction temperature			-55 to 175		°C	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.45	1.70	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.80	2.20	V
Dynamic	characteristics	·					
Q _r	recovered charge	$I_F = 10 \text{ A}; \text{ d}I_F/\text{d}t = 500 \text{ A}/\mu\text{s}; V_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	14.5	-	nC

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	<u></u>	к-Ң-А
2	К	cathode [1]		001aaa020
3	А	anode		
mb	К	mounting base; connected to cathode		

[1] It is not possible to connect to pin 2 of the TO252 package.

6. Ordering information

Table 3. Ordering information							
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date	
WNSC5D10650D	TO252	WNSC5D10650D6J	Reel	2500	TO252NS	14-Nov-2016	

7. Marking

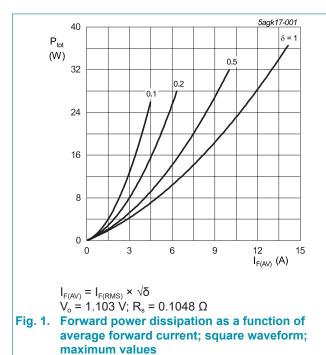
Table 4. Marking codes						
Type number	Marking codes					
WNSC5D10650D	WNSC5D 10650D					

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V _{RWM}	crest working reverse voltage			650	V
V _R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; T _{mb} ≤ 140 °C; Fig. 1; Fig. 2; Fig. 3		10	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 140 °C; square-wave pulse		20	A
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		55	А
	forward current	t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse		540	А
l ² t	I ² t for fusing	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		15.125	A ² s
T _{stg}	storage temperature			-55 to 175	°C
T _j	junction temperature			-55 to 175	°C



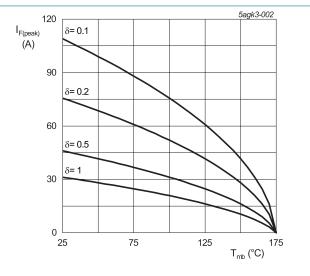
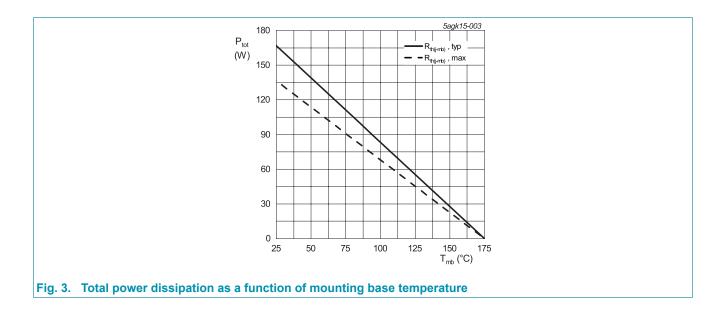


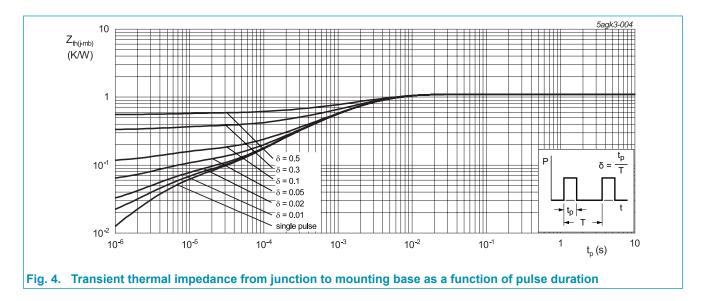
Fig. 2. Current derating as a function of mounting base temperature

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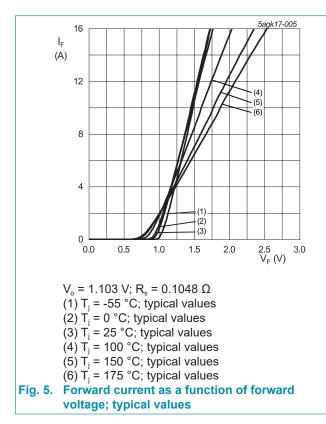
9. Thermal characteristics

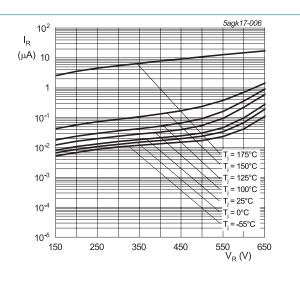
Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 4</u>		-	0.9	1.1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	50	-	K/W



10. Characteristics

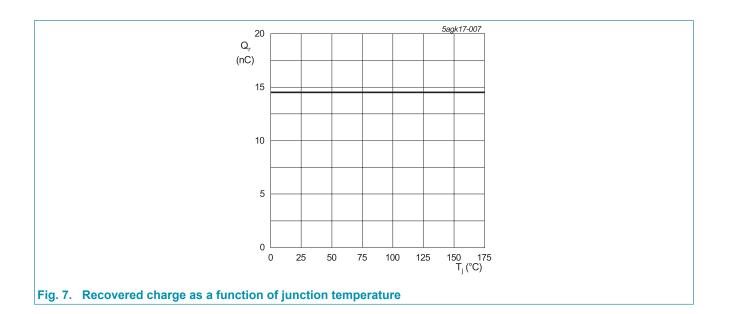
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
V_{F}	forward current	I _F = 10 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.45	1.70	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.80	2.20	V
		I _F = 10 A; T _j = 175 °C; <u>Fig. 5</u>		-	2.00	2.30	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>		-	0.5	50	μA
		V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u>		-	25	250	μA
Dynamic	characteristics						
Q _r	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{2}$		-	14.5	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C		-	323	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C		-	38	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C		-	35	-	pF
E _{as}	non-repetitive avalanche energy	$I_R = 4.9 \text{ A}; T_{j(init)} = 25 \text{ °C}; L = 5 \text{ mH}$		60	-	-	mJ



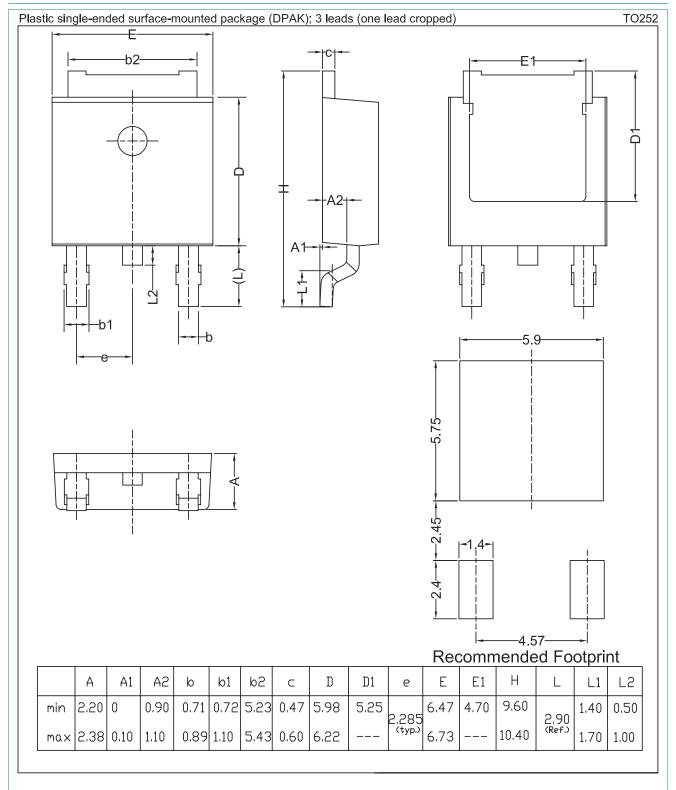




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11. Package outline



WNSC5D10650D Product data sheet

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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